

Current Status and Future Possibilities of High Harmonic (HHG) Sources for Characterization/Metrology in the Semiconductor Industry

Brennan Peterson, Erik Hossler, Margaret Murnane, Henry Kapteyn

Thanks to

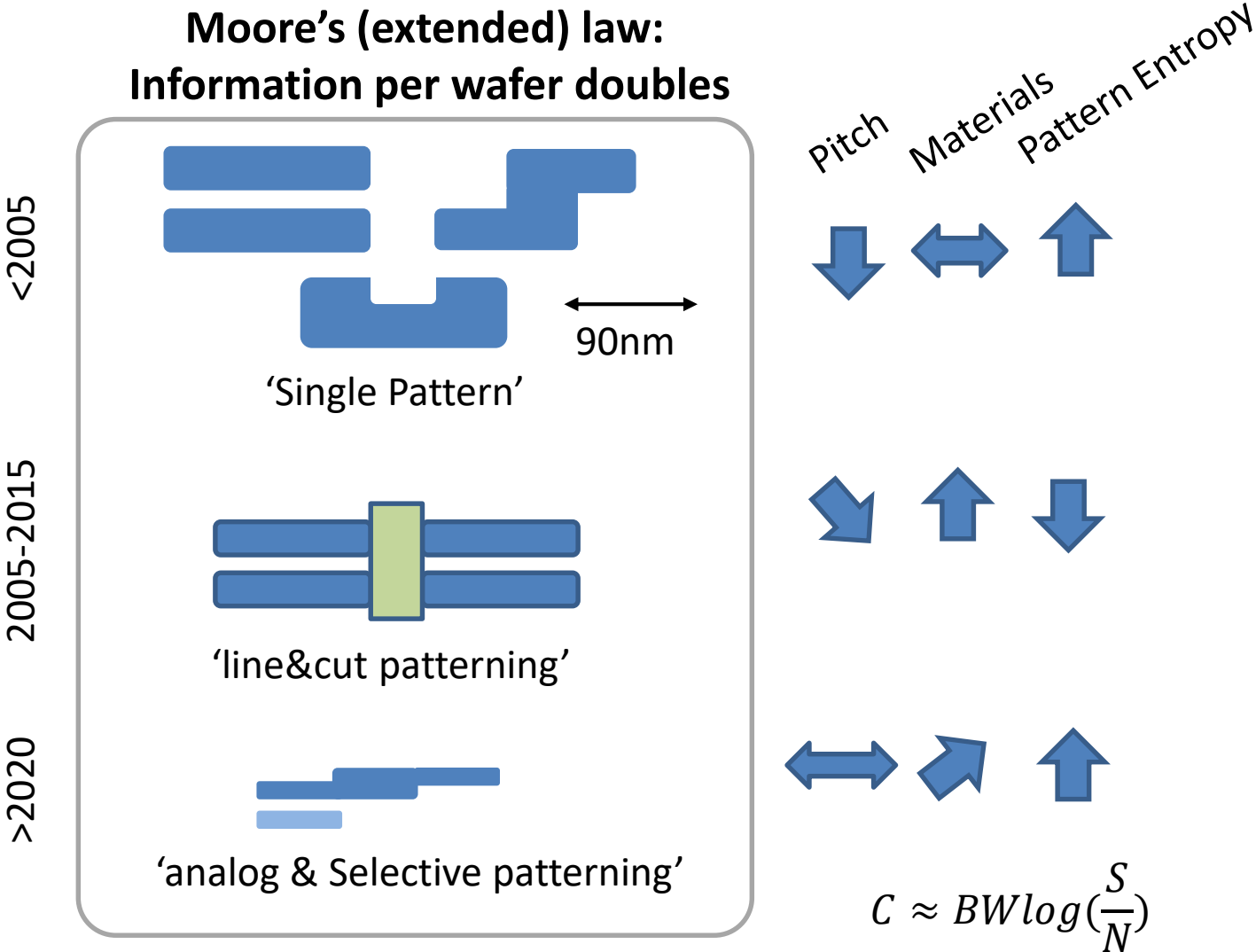
KM Group @ JILA , STROBE

Margaret Murnane, Henry Kapteyn (all the material!)

Dan Hickstein, Scott Domingue, Matt Kirchner, Sterling Backus, Daisy

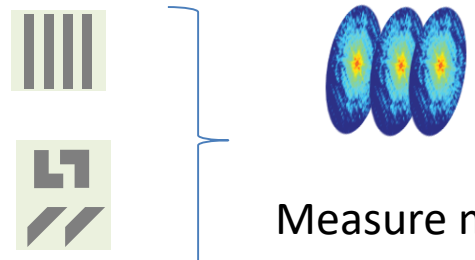
Raymondson @ KMLabs

Obligatory Moore's law slide



Metrology challenges

Mapping Challenge



1E5 metro 1E16 wfr

Measure more
Compress/ extrapolate

Information

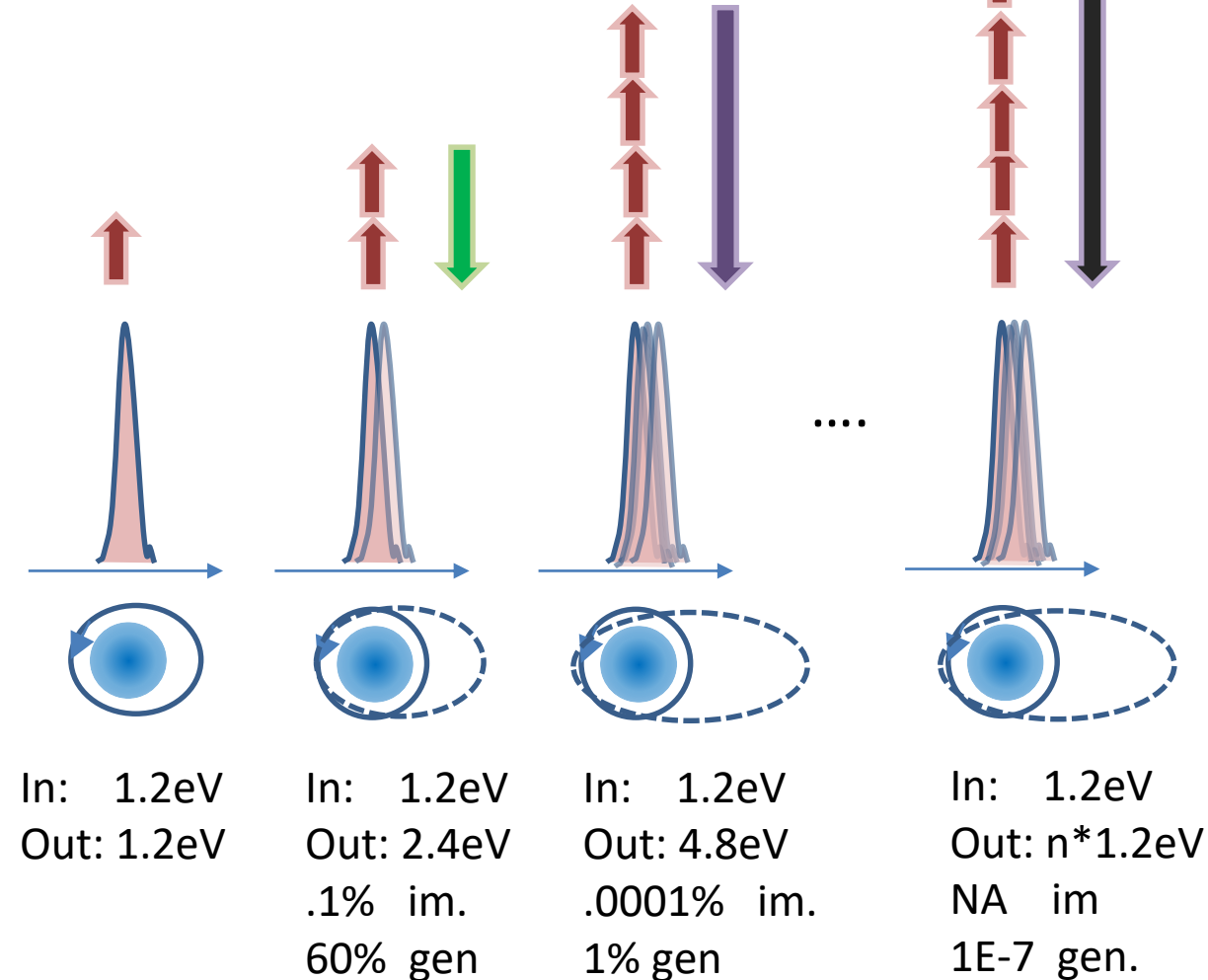
$$I_{met} \approx S * C_i * P_i * \log(F)/Pa$$

S: sampling
C: channels
P: probed states (like polarization)
F: features
Pa: parameters (corr.)

BP's caveat: it never gets easier

Summary and approximate understanding of (High) harmonic generation

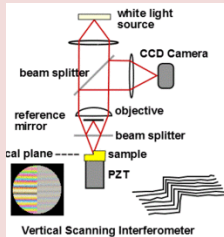
- Optical microscopy with ultrafast pulses
- What is High Harmonic Generation (HHG)
 - Generate laser like light at 10nm-200nm
- Why:
 - Take advantage of wavelength (λ/NA)
Take advantage of light microscopy/control
 - Take advantage of energy (eV)
- Applications of VUV/EUV light
- Novel/useful semiconductor applications



'Low Harmonic' use-cases in microscopy are dramatically better due to source improvements

Source/Microscopy

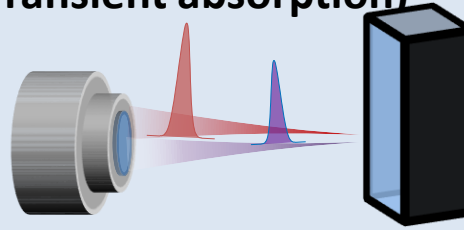
Interferometry



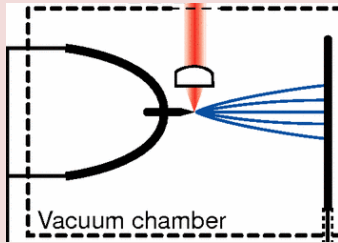
Ultrafast spectroscopy*

Needs femtosecond pulses

Pump-probe spectroscopy (Transient absorption)



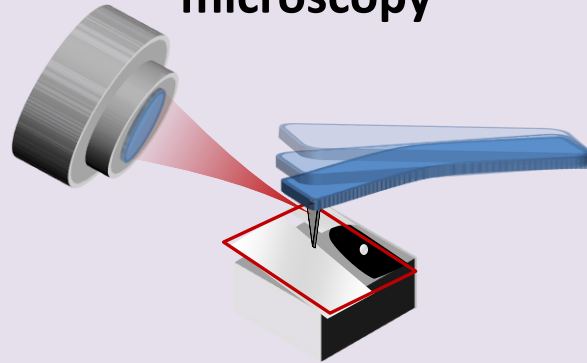
TEM-tip source enhancement*



Kerr/phase microscopy



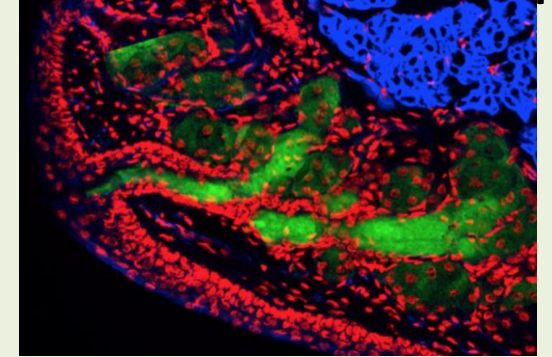
AFM-tip Nanospectroscopy and microscopy



Ultrafast microscopy

Needs femtosecond pulses at ~1 MHz rep rate

Coherent Raman microscopy



Alfonso-Garcia et al., *J. Biomedical Optics*, **19**, 071407 (2014).
<https://doi.org/10.1117/1.JBO.19.7.071407>

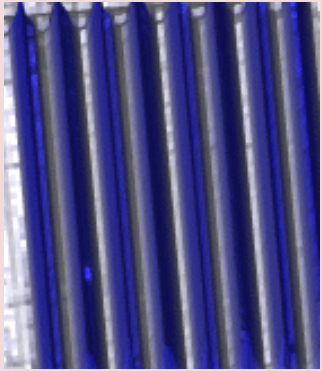
*HG nonlinear microscopies SFG, TA, FL, 2D-IR



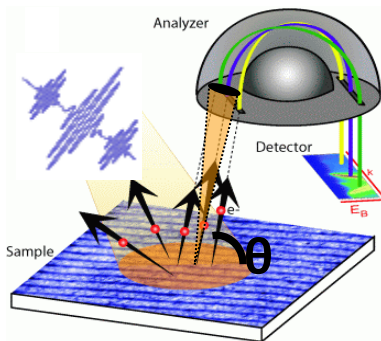
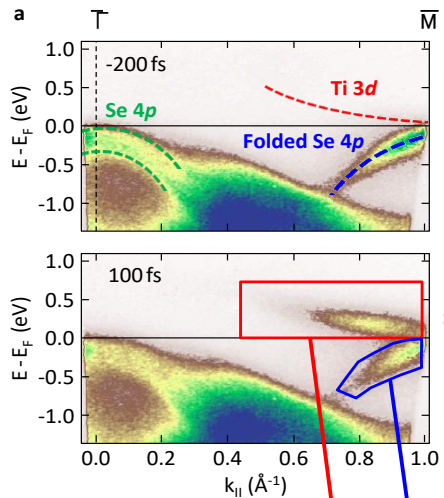
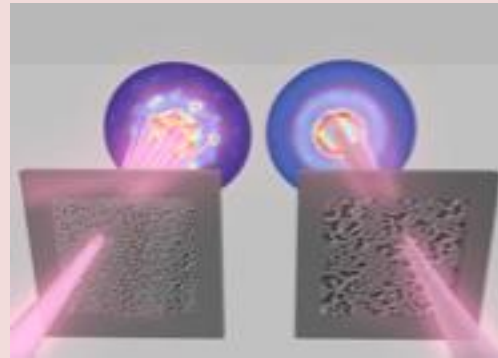
Squier/Bartels CLEO 2018

Extending optical microscopy to $>20\text{nm}$ wavelengths using HHG

Diffraction imaging/ interferometry

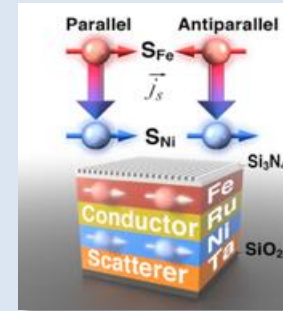


μ -scatterometry

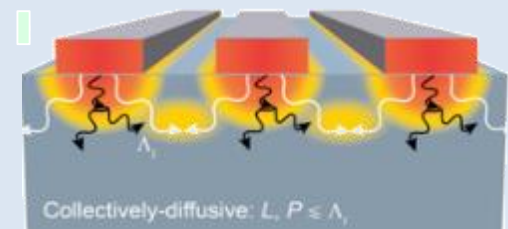
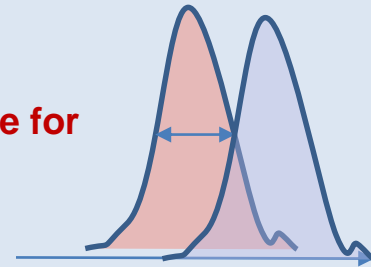


Novel SEM/TEM/APT probe

IR pump/EUV probe (Band edge) Magneto-optical Kerr effect



EUV pump/IR probe for photoresist



EUV pump/*probe for nanomechanics

Band structure and electron dynamics

200→6nm wavelengths, <100fs pulses of laser-like light, at uW power levels

Maximum wavelength $\sim \lambda_p^2$

400nm→60nm (20eV)

800nm→13nm (100eV)

3000nm→1.4nm (800eV)

Output (in ph/s)

- $\sim 10^{11}$ 13nm
- $\sim 10^{13}$ 30nm
- $\sim 10^{15}$ 130nm

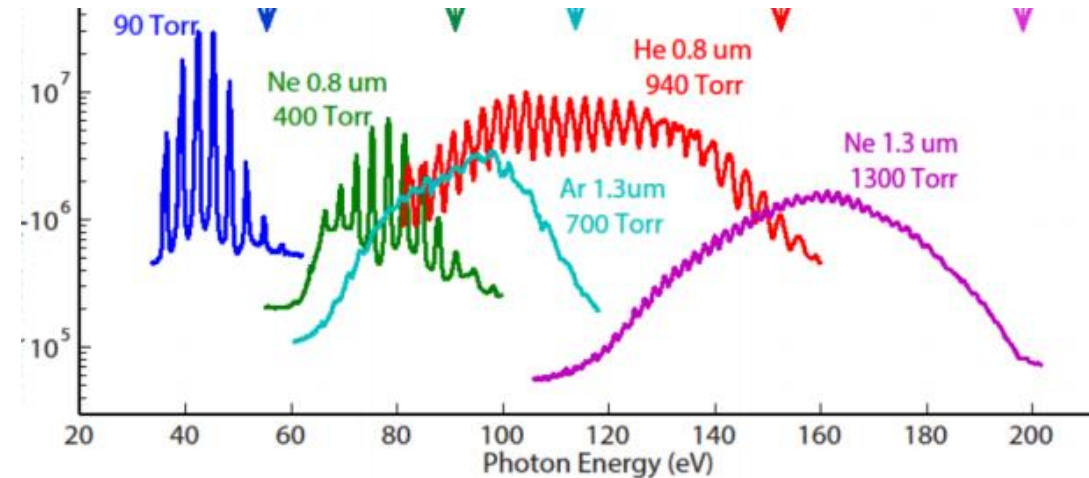
Energies

- 10eV: oxide/vacuum bonds
- 80eV: magnetic edges
- 94eV: 13.5nm

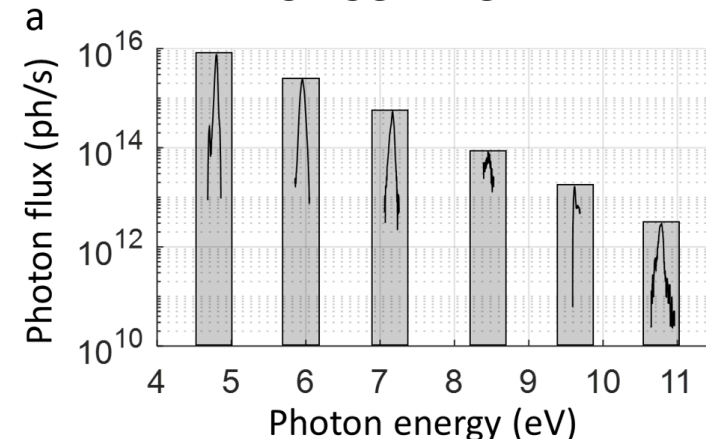
Brightness

- $\sim 4 \cdot 10^9$ W/m²/Sr @ 13 eV : uW level

'tabletop EUV' 20-200eV (60→6nm)



'5-15eV' VUV



Early data 15⁺eV



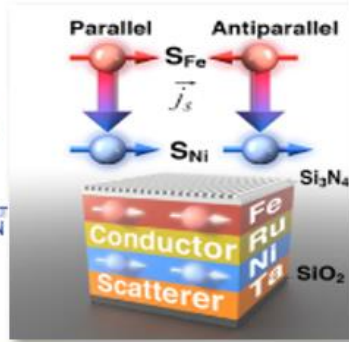
Multiple solid state physics and materials science use cases

HHG experimental references

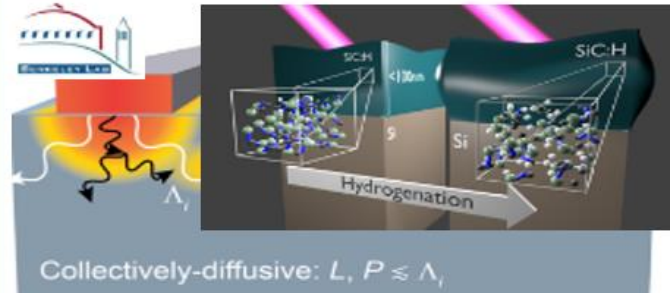
Uncovering new materials/nano science

Spin dynamics in magnetic materials

Science Advances, in press (2018)
PRB, **97**, 024433 (2018)
PRB **94**, 220408 (2016)
PRL **110**, 197201 (2013)
PNAS **109**, 4792 (2012)
Nat Comm. **3**, 1037 (2012)

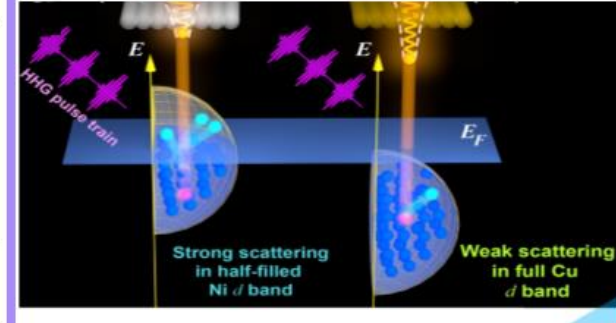


Nanoscale mechanical properties, energy transport

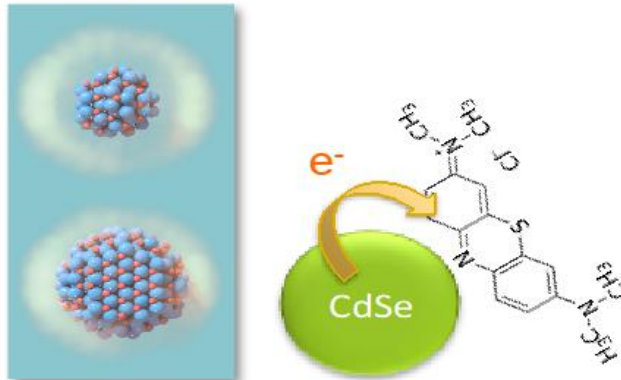


Nature Mat. **9**, 26 (2010); PRB **85**, 195431 (2012) PNAS **112**, 4846 (2015);
Nano Lett. **16**, 4773 (2016); Nano Letters **17**, 2178 (2017)

Dynamic band structure via ARPES

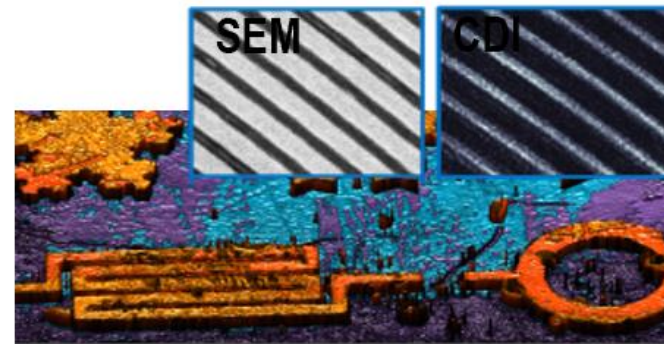


Charge transport in nano-materials

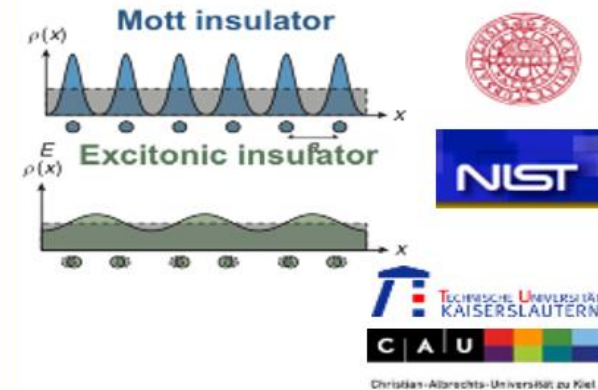


Nano Lett. **13**, 2924 (2013)
JACS **137**, 3759 (2015)

1st sub-wavelength EUV / X-ray imaging



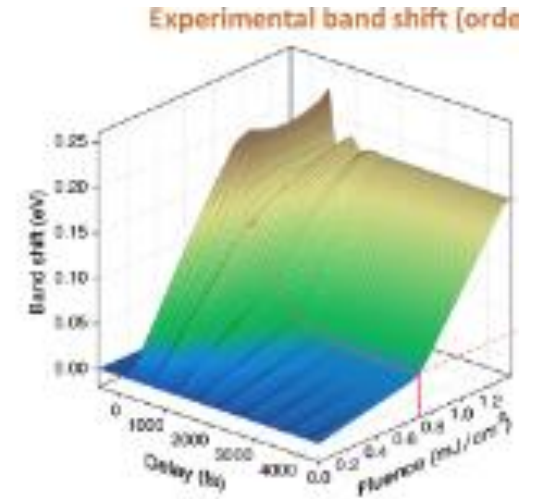
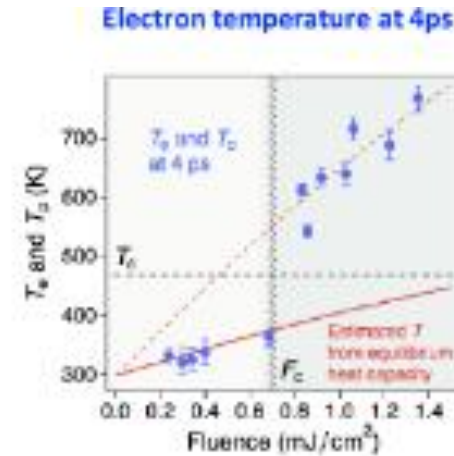
Science **348**, 530 (2015); Ultramicroscopy **158**, 98 (2015)
Nano Lett. **16**, 5444 (2016); IQT **8**, 18 (2016); Nature Photonics **11**, 259 (2017); Optica **4**, 1552 (2017)



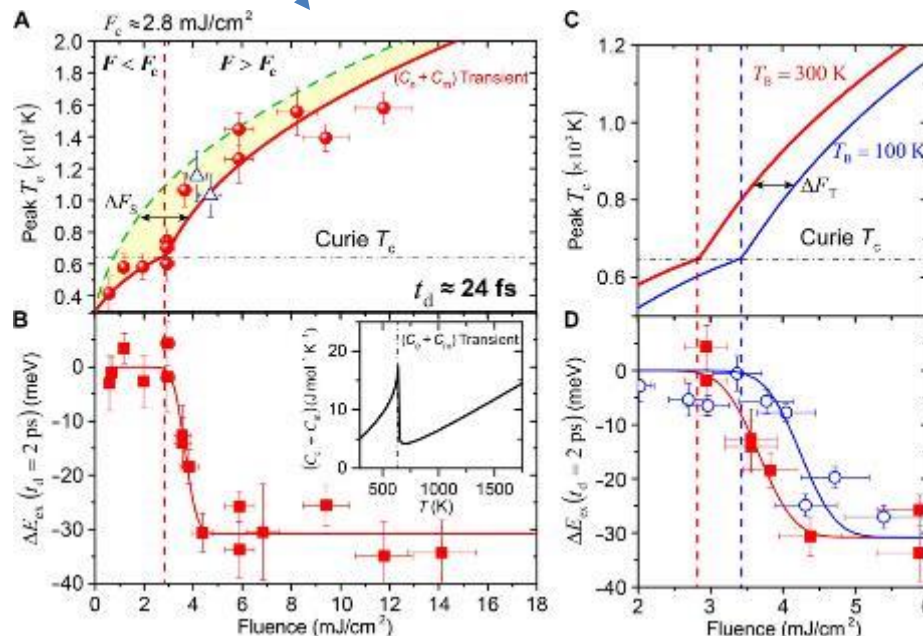
PNAS **114**, E5300 (2017)
Science Advances **3**, e1602094 (2017)
Science **353**, 62 (2016)
Science **353**, 28 (2016)
Nature **471**, 490 (2011)
Nat. Comm. **3**, 1069 (2012)
PRL **112**, 207001 (2014)
PRB **92**, 041407 (2015)
Nature Comm. **7**, 12902 (2016)

Material band structure and evolution can be measured with laser photoemission (ARPES)

- New metastable phase seen in TaSe2
- Magnetization dynamics studied via electron temperature in Ni (Tengdin et al)



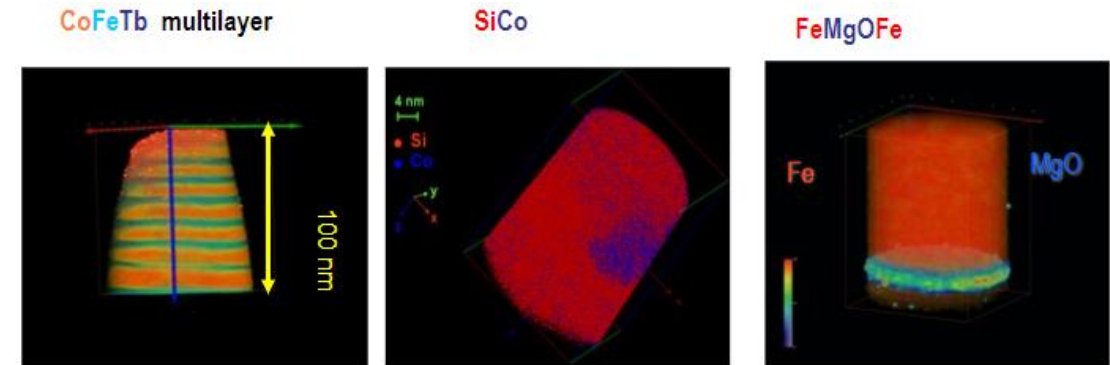
Ultrafast Phenomena Xun Shi et al.
Science Advances 01 Mar 2019:
Vol. 5, no. 3, eaav444



PNAS **114**, E5300 (2017)
Science Advances **3**, e1602094 (2017)
Science **353**, 62 (2016)
Science **353**, 28 (2016)
Nature **471**, 490 (2011)
Nat. Comm **3**, 1069 (2012)
PRL **112**, 207001 (2014)
PRB **92**, 041407 (2015)
Nature Comm. **7**, 12902 (2016)

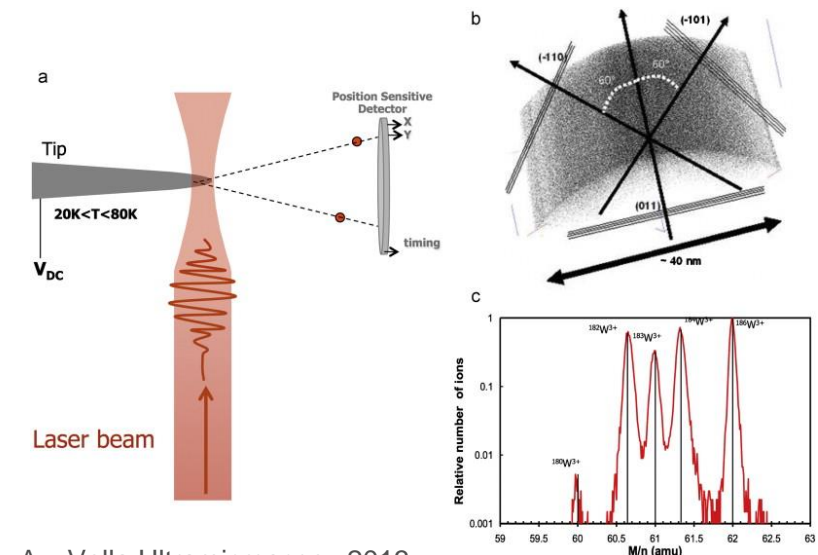
Tip based photoemission: APT: unique opportunity to do single photon ionization and surface heating

- APT: Generation of UV light (might) benefit due to
 - High energy per pulse \rightarrow uniform absorption
 - Multiphoton surface enhancement \rightarrow single photon at $>11\text{eV}$.
 - High pulse rate (MHz)



A. Grenier et al. JAP 102,033912 2008. Gilbert et al. Ultramicroscopy 107,767,2007. Talaat Al Kassab, IJMR 99,5,2008

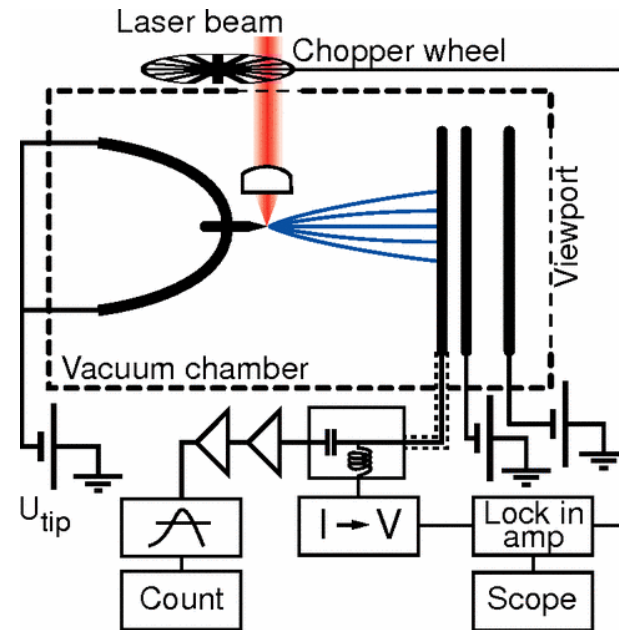
- Diagnostics
 - Direct diagnostic tip imaging possible



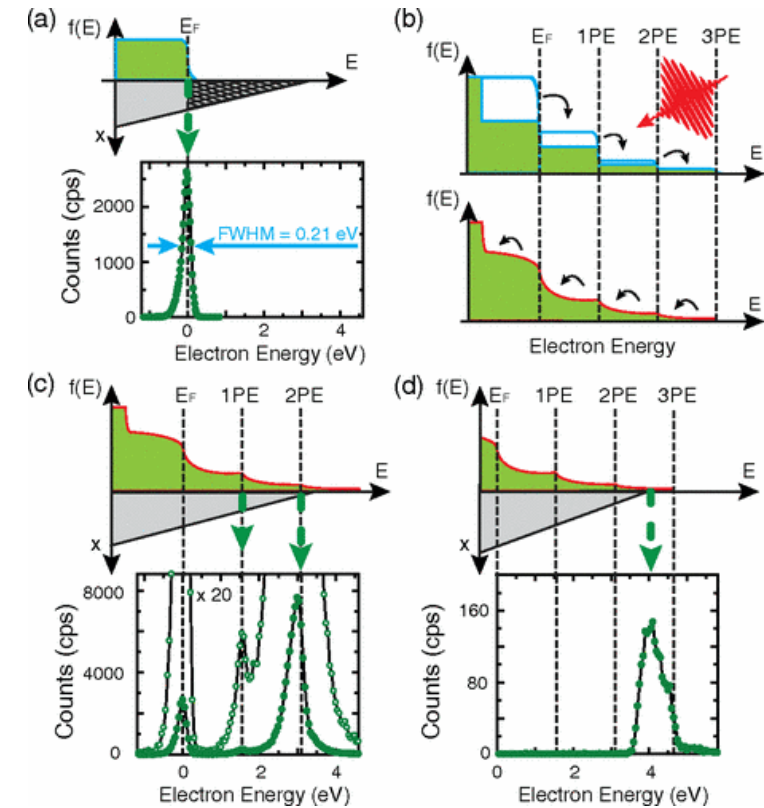
A. Vella Ultramicroscopy 2013

Lasers for ultrafast electron emission: UV avoids multiphoton effects

- Using the energy to drive emission
 - Time resolution!
- VUV (~6eV) energies can directly ionize for high efficiency electron generation
 - This can also greatly increase effectiveness, as we can directly ionize, rather than rely on multiphoton processes
 - Or use a very good pulse, to improve MP efficiency!



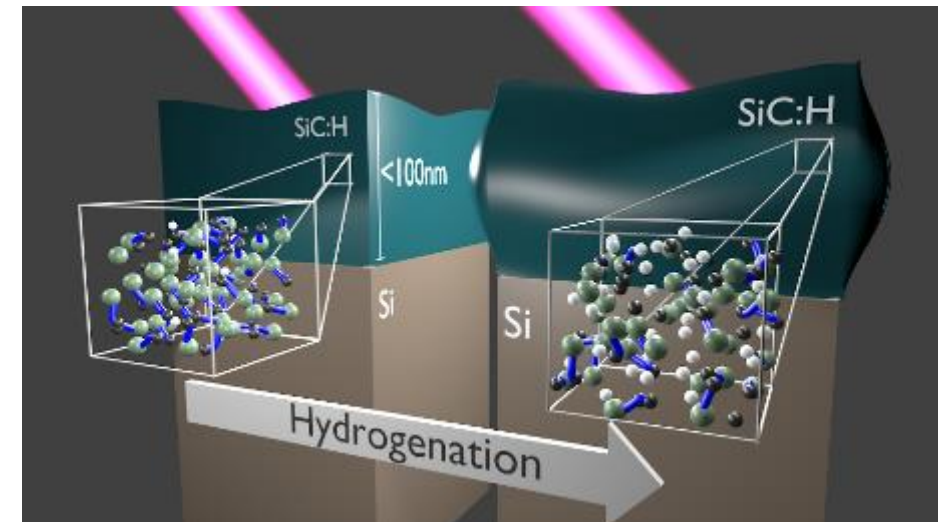
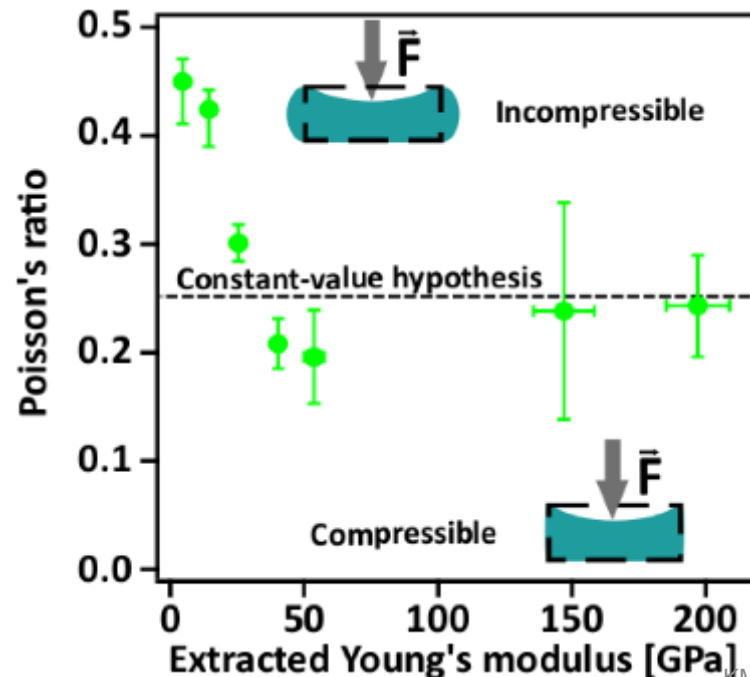
Peter Hommelhoff et al
Phys. Rev. Lett. **96**, 077401 – Published
21 February 2006



Hirofumi Yanagisawa et al.
Phys. Rev. Lett. **107**, 087601 – Published 16
August 2011

Characterization of elasticity on thin films: 11-50 nm films

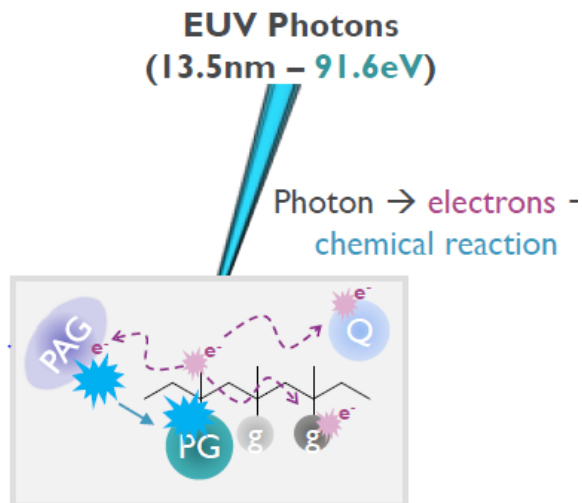
- Techniques such as nano-indentation are unreliable for films <100 nm
 - Can measure the Young's modulus but not the Poisson's ratio
- For SiC:H thin films, doping breaks bond coordination and changes the mechanical properties: critical for semiconductor reliability
- Material changes from being compressible to incompressible



Nano Lett. **16**, 4773 (2016); *Nano Letters* **17**, 2178 (2017)

Pump/Probe for Magnetic scattering and EUV resist fundamentals

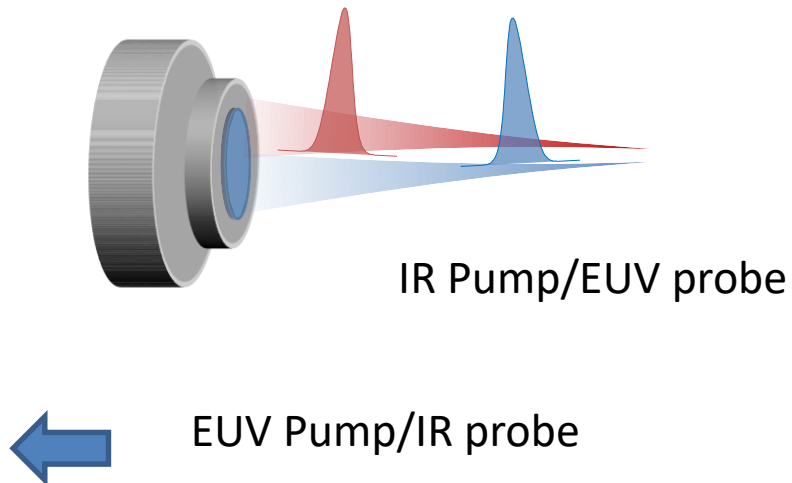
- EUV magneto-optic spectroscopies can very sensitively read out the magnetic state of each layer and element in a magnetic multilayer or alloy
- EUV pump/IR probe to measure photoresist dynamics



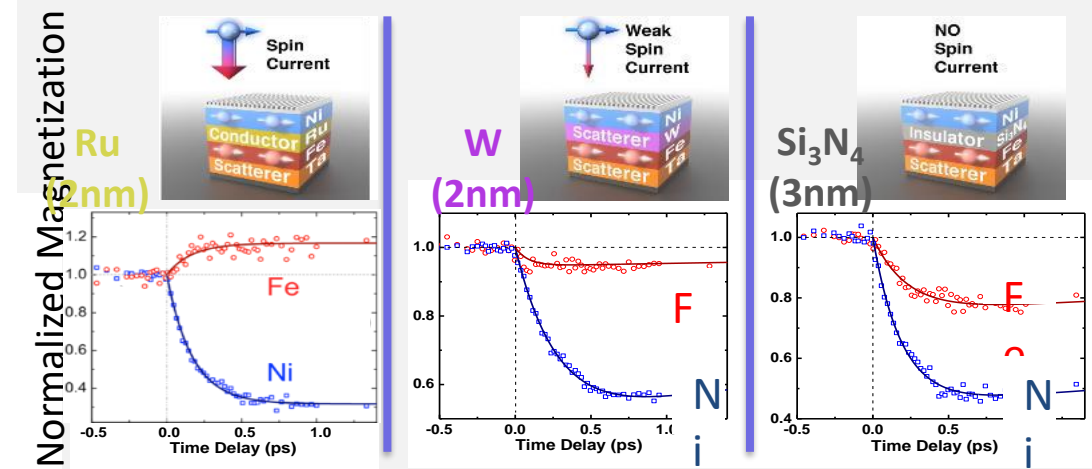
Multiple chemical reactions take place...What is the balance of these reactions to acid reaction ?

John Petersen SPIE 2019

PURIC



Science Advances **4**, 9744 (2018)
PRB, **97**, 024433 (2018)
PRB **94**, 220408 (2016)
PRL **110**, 197201 (2013)
PNAS **109**, 4792 (2012)
Nat. Comm. **3**, 1037 (2012)



PRL **110**, 197201 (2013)
Nat. Comm. **3**, 1037 (2012)

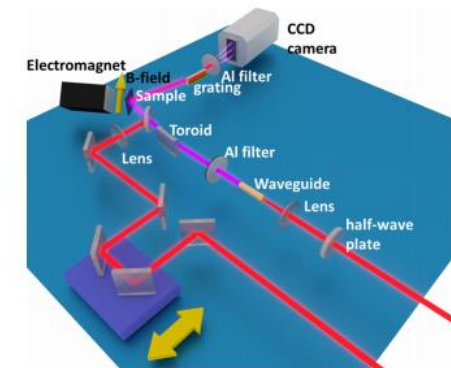
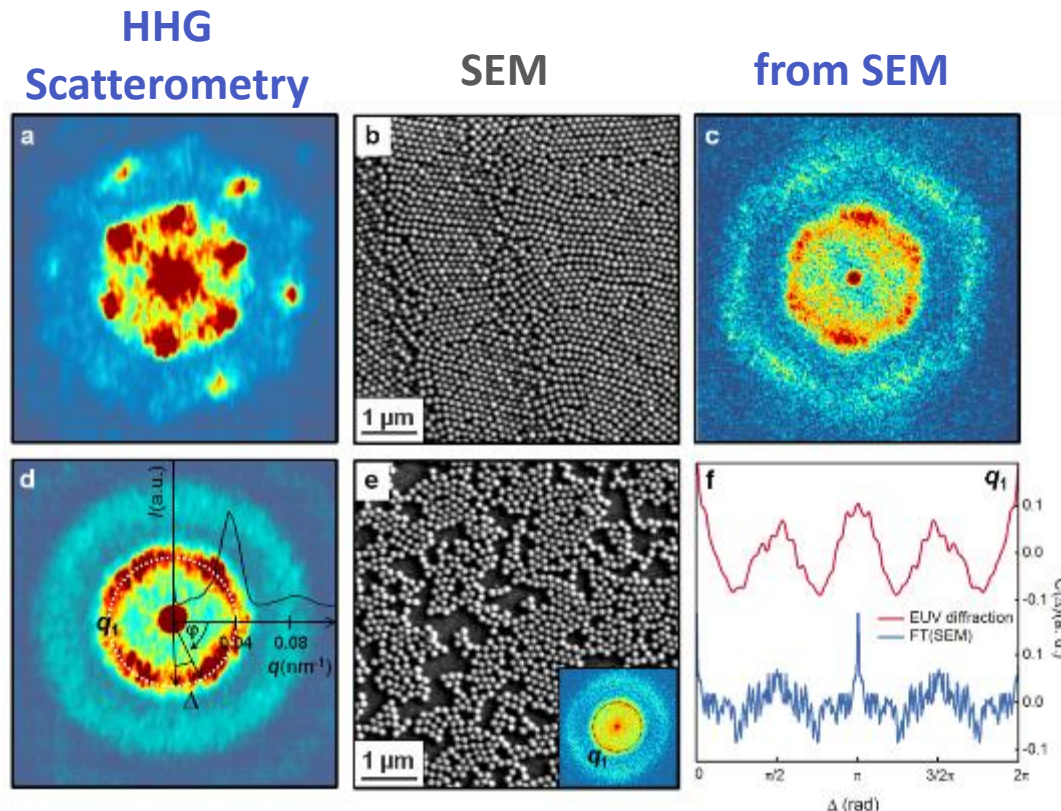
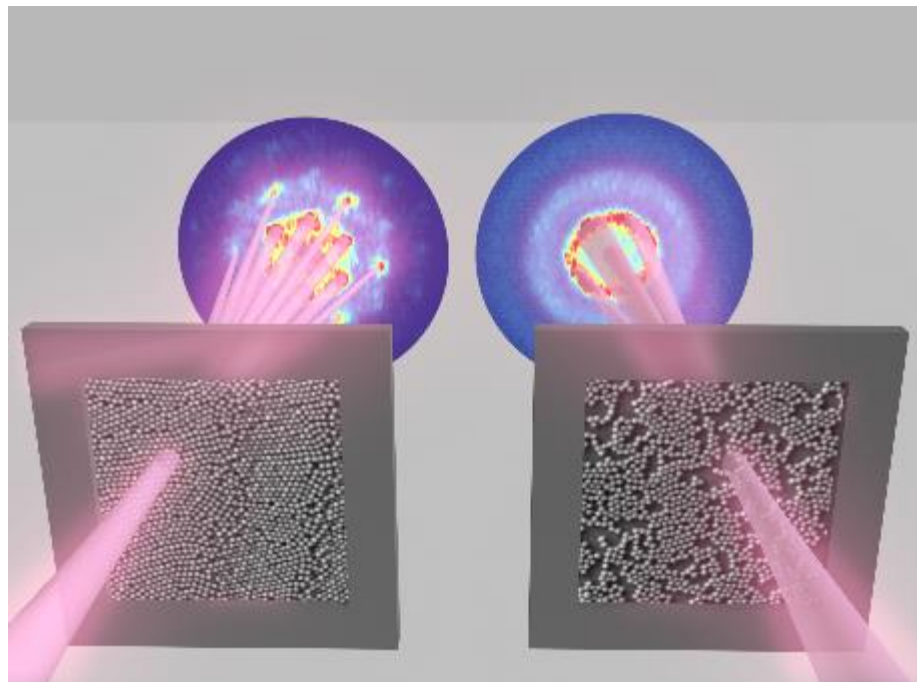


FIG. 2. Experimental setup to implement D-MOE. A half-wave plate is used to rotate the linear polarization of the driving laser, and hence the polarization of the HHG beam.

PRB 2018 D Zusin

Diffraction: nm-scale order in self-assembled materials

- Simultaneously characterize nanospheres size, symmetry, distribution within grains
- Small-angle Bragg scattering from self-assembled materials

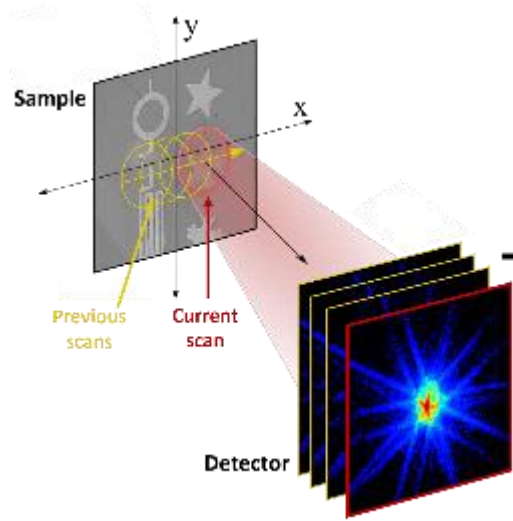


Mancini, et al. (2017)

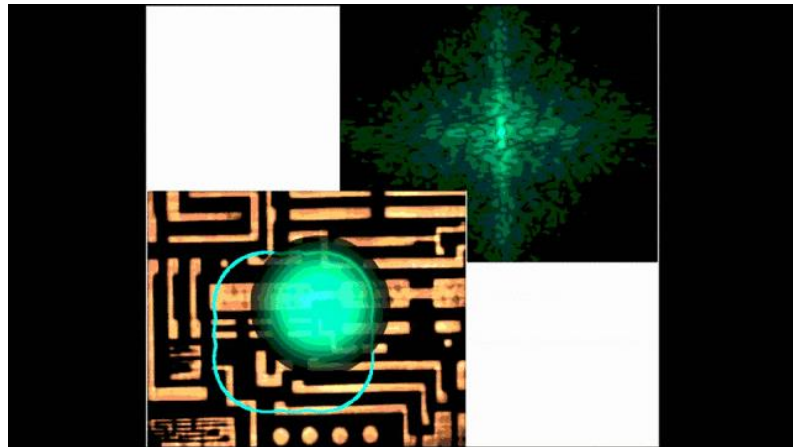


Diffraction imaging

Diffraction imaging is critically useful at *UV wavelengths → Coherent Diffraction Imaging



- Coherent Diffraction Imaging
 - Shine a coherent beam on an object
 - Record scatter on imaging detector
 - Use computation to build image of the surface that scattered the light



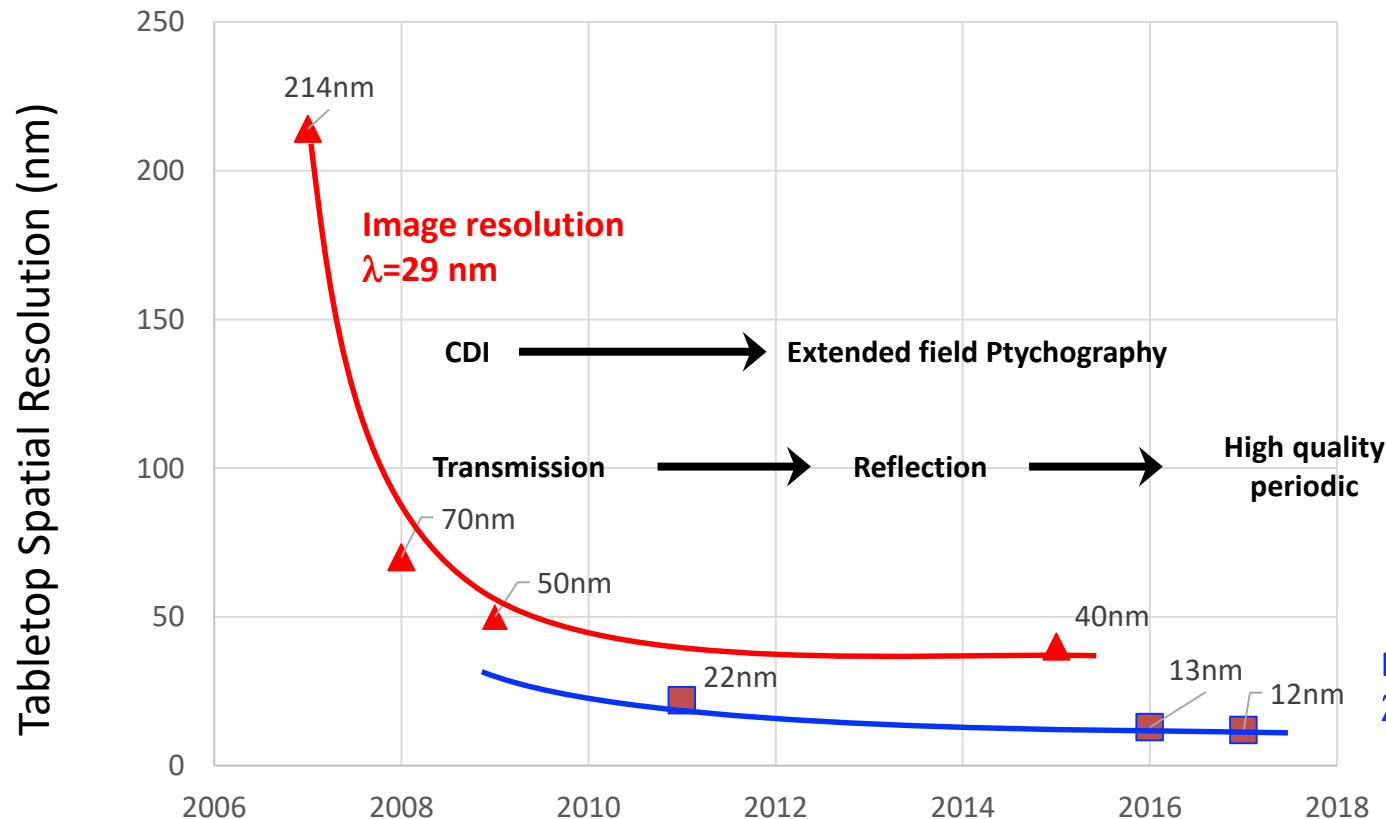
‘don’t use a lens to take a Fourier Transform, use a computer’

Benefits:

- Ptychography increases robustness/noise immunity
- Reconstruction on arbitrary objects (no regularity needed)

EUV coherent imaging has continued to improve in the lab


- Record spatial resolution of 0.9λ: 12.6nm using 13.5nm XUUS HHG beams
- Full field imaging of near-periodic structures, with record speed, resolution
- Can scale to shorter wavelength, higher resolution, deeper penetration



JILA
NISTCU



Science **348**, 530 (2015); Nature Photonics **11**, 259 (2017)

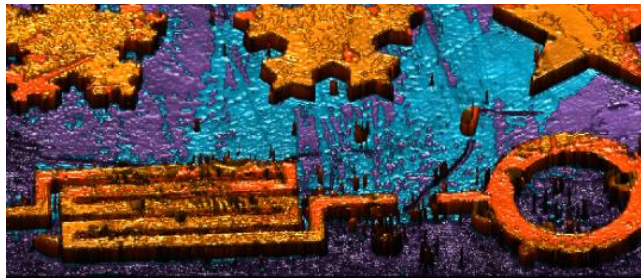
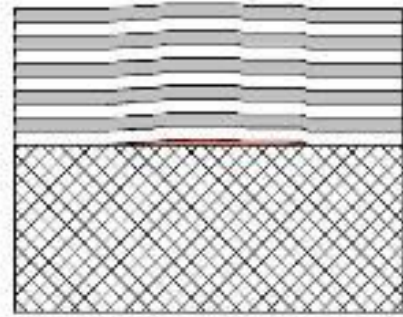
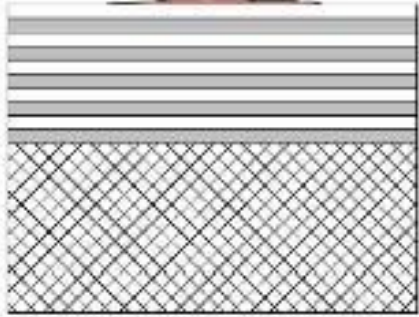


Semiconductor use cases for diffractive imaging and EUV/IR pump probe

Fab/Mask imager: EUV mask defect review

Amplitude Defect

Phase Defect



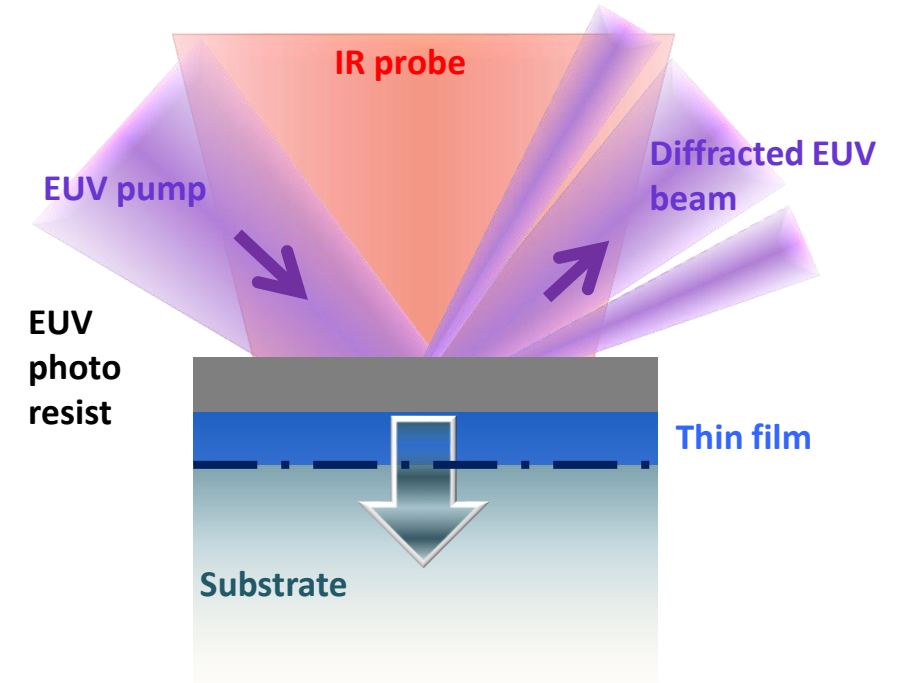
- Computational, aberration free phase reconstruction→
 - Phase image on mask is the outgoing wave: perfect for mask defect review
 - ‘Direct’ computational aerial image
 - 3D image
- High NA capable ($\sim .6\text{NA}$)
- Fast (reflection on masks is high!)

EUV pump/IR probe for direct resist decomposition measurement

Coupled IR probe (different detection possible) and EUV (13.5nm) pump

- Direct detection of EUV resist kinetics
 - Measure time evolution of exposure
- Measurement on substrate to determine interactions from different underlayers

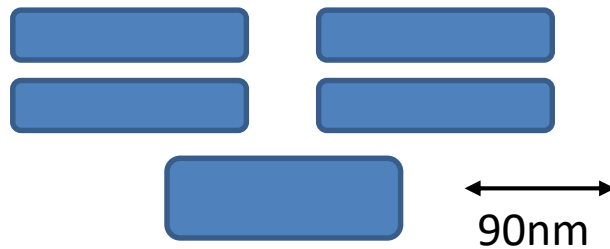
Direct calibration of photoresist models may be possible



Defectivity and metrology are different in a non-scaling era

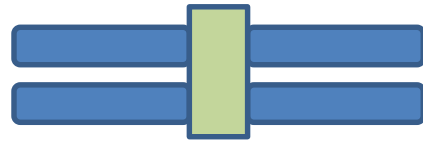
Moore's Law era

<2005



'Single Pattern'

2005-2015



'line&cut patterning'

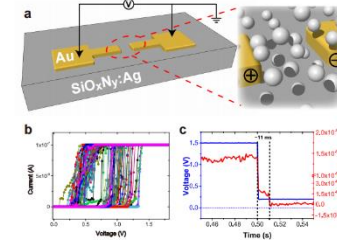
>2020



'analog & Selective patterning'

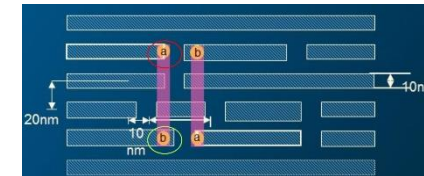
Post-Moore's Law era

- Physical shrink
 - Material led shrink*New materials*

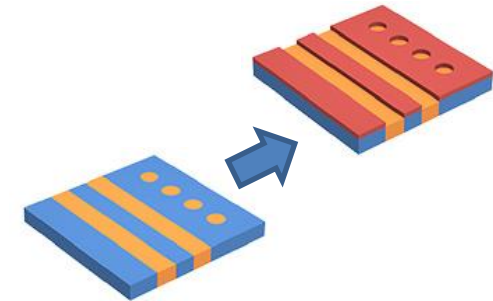


Zhongrui Wang et al Nature Materials v16, p101-108 (2017)

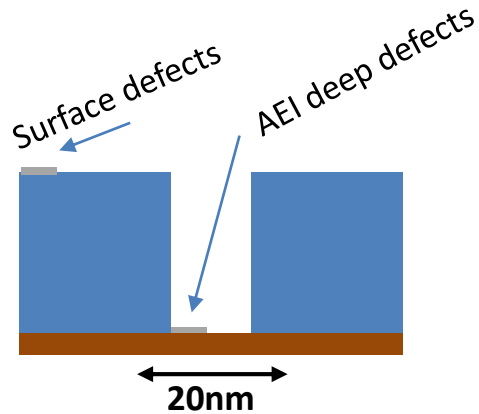
- Median control
 - Stochastic control*New strategies*



- Patterning
 - Selective patterning*New errors*



Defect Review & CD metrology



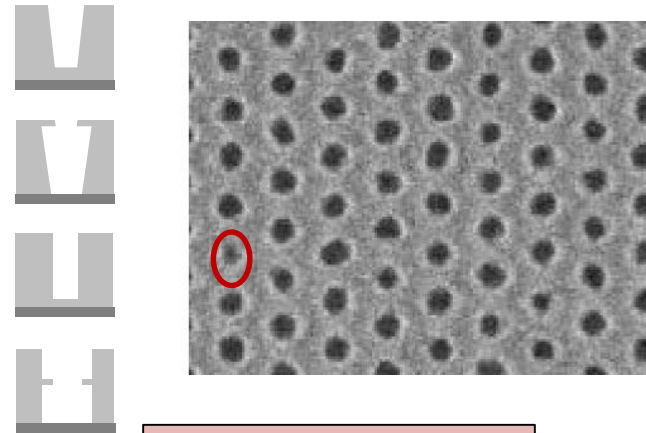
Defects at bottom of Via

Issue:

- Defect deep in feature cannot be reviewed by SEM

EUV imaging answer:

- EUV optical penetration in gives phase visibility to bottom-of-contact items



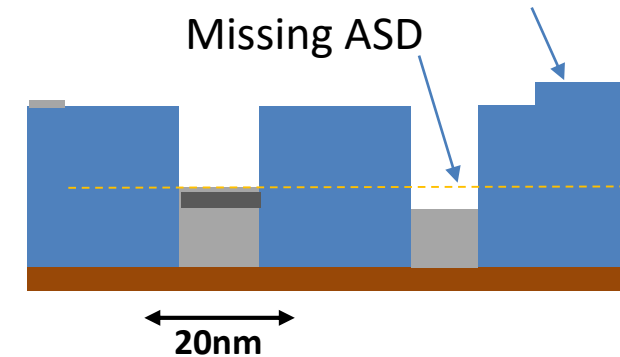
Stochastic defects

Issue:

- Many critical defects are random
- Median CD not sufficient

EUV imaging answer:

- Image large FOV
- Measure direct distribution



Topographic defects

Issue:

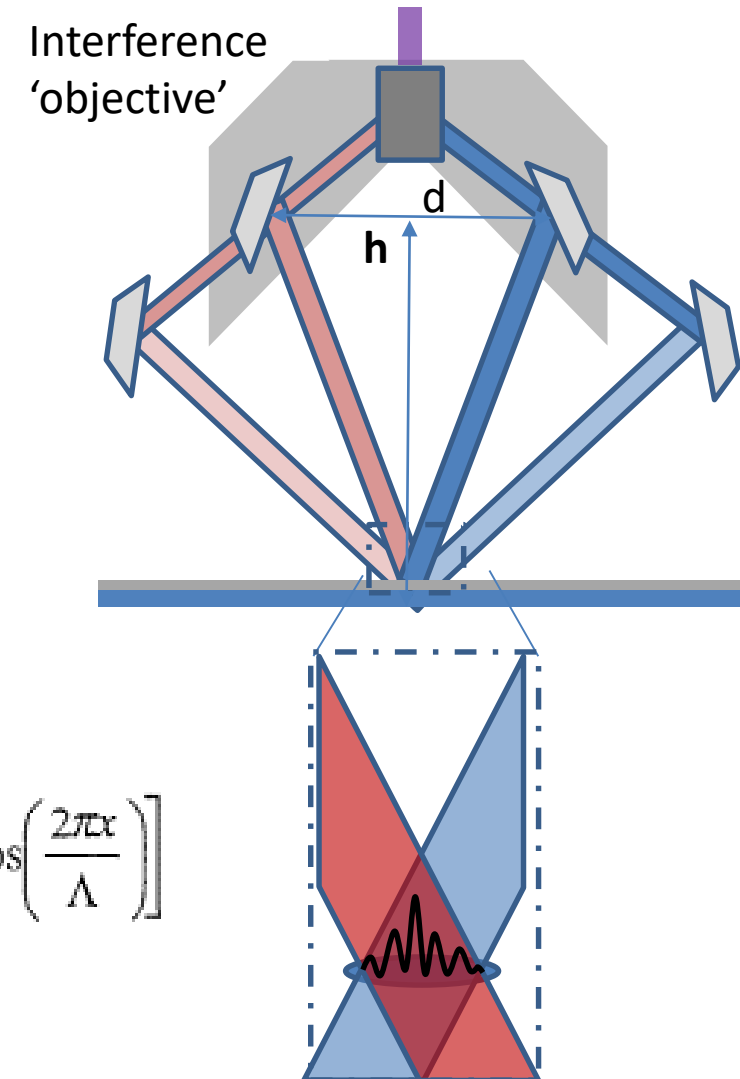
- Height/coating defects not measureable with SEM

EUV imaging answer:

- Direct height via phase
- Sensitive to selective deposition variation

Interferometric printing for resist qualification

- Multi-resolution printing of lines at 10-40nm pitch
- Variable contrast across aperture and as a function of printed pitch
- Variable contrast in envelope function
- Cost and throughput allow
 - Point or use qualification
 - Aging tests
 - Post manufacture testingAll without need for a full EUV system

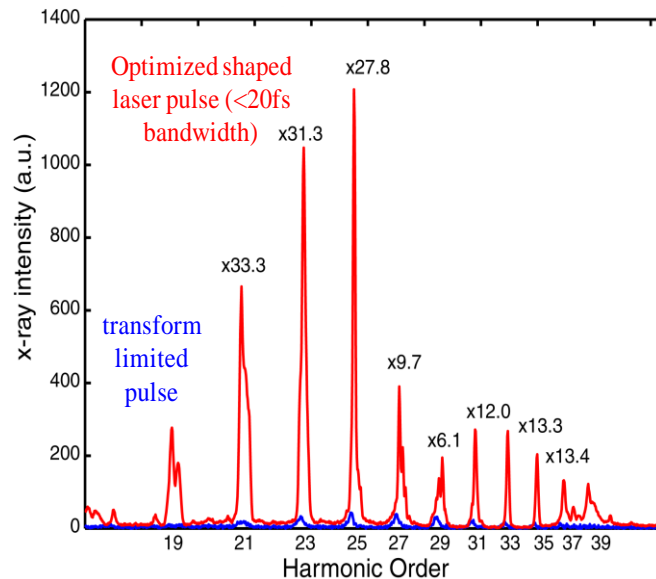




What is next

Where next: 100x faster image, 10,000 faster solution time

More photons (uW)



HHG can improve by 10-30x
Top: Randy Bartels

Better Systems



Better Software

Ptychography is uniquely good for DL/NN:
→ Clear forward solution/model
→ high amount of data
→ computationally difficult inversion

Solving Fourier ptychographic imaging problems via neural network modeling and TensorFlow

SHAOWEI JIANG,^{1,3} KAIKAI GUO,^{1,3} JUN LIAO,^{1,3} AND GUOAN ZHENG^{1,2*}

¹Biomedical Engineering, University of Connecticut, Storrs, CT, 06269, USA

²Electrical and Computer Engineering, University of Connecticut, Storrs, CT, 06269, USA

³These authors contributed equally to this work

*guoan.zheng@uconn.edu

Deep learning-based super-resolution in coherent imaging systems

Tairan Liu^{1,2,3†}, Kevin de Haan^{1,2,3†}, Yair Rivenson^{1,2,3†}, Zhensong Wei^{1†}, Xin Zeng¹, Yibo Zhang^{1,2,3}, and Aydogan Ozcan^{1,2,3,4,*}

¹Electrical and Computer Engineering Department, University of California, Los Angeles, CA, 90095, USA.

²Bioengineering Department, University of California, Los Angeles, CA, 90095, USA.

³California NanoSystems Institute (CNSI), University of California, Los Angeles, CA, 90095, USA.


⁴Department of Surgery, David Geffen School of Medicine, University of California, Los Angeles, CA, 90095, USA.

† Equally contributing authors

*ozcan@ucla.edu

(many, many articles)

What is next: finishing

- 
-
- There is incredibly useful science that can be uncovered with HHG
 - It takes *doing* and *completing*